

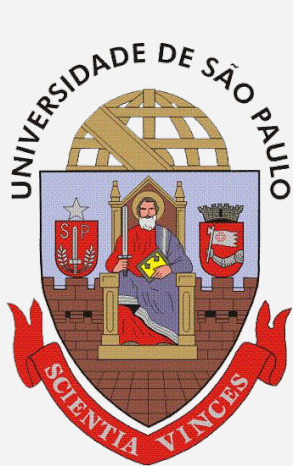
Synchrotron Light Source X-ray Detection with Low-Gain Avalanche Diodes

*13th International "Hiroshima" Symposium on
Development and Applications of Semiconductor Tracking Detectors (HSTD13)*
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On behalf of the SCIPP and Sao Paulo group

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Overview



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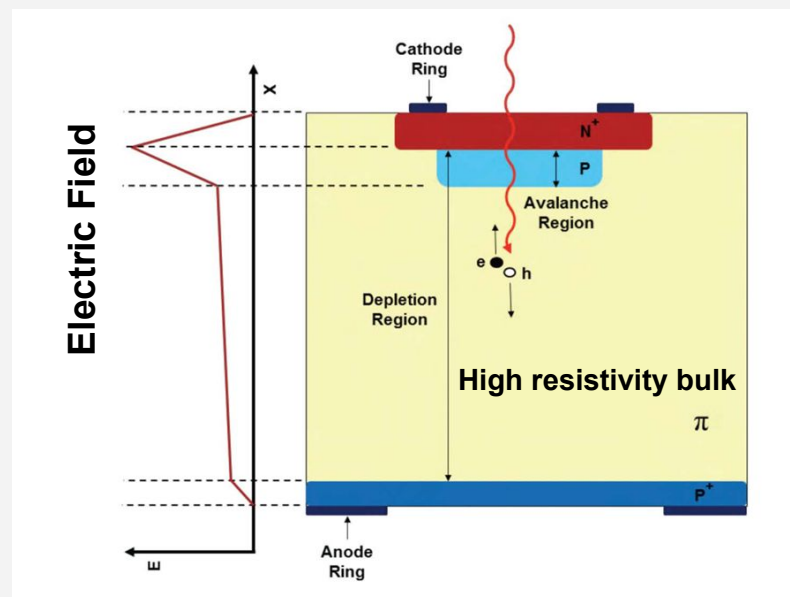
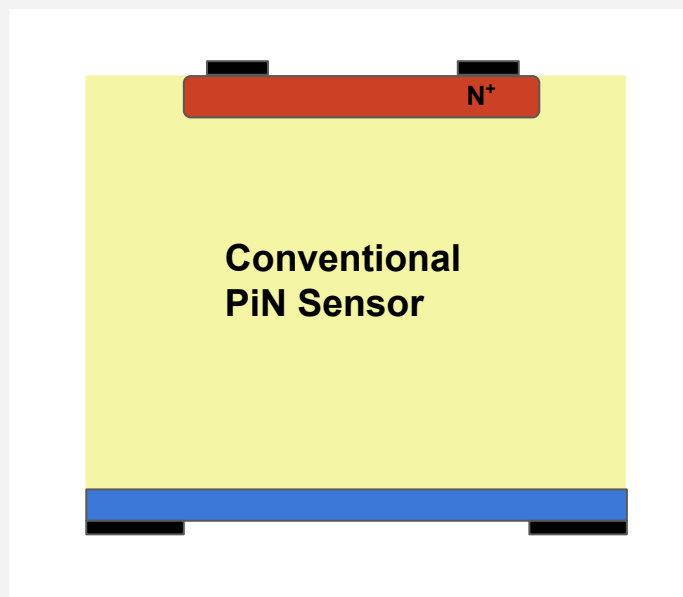
Introduction to LGAD





Low Gain Avalanche Diode

- The low gain avalanche detector (LGAD) is the state-of-the-art technology in time measurement for charge particles, with the following features:
 - Provide moderate internal gain of 5 to 50 \Rightarrow can be used for small signal detector (low energy X-rays).
 - Active thickness of 20 to 50 μm \Rightarrow fast collection time, high frame rate capability.
 - Timing resolution is 20 ps or better before high dose irradiation for MIPs.



The SSRL Testbeam Setup



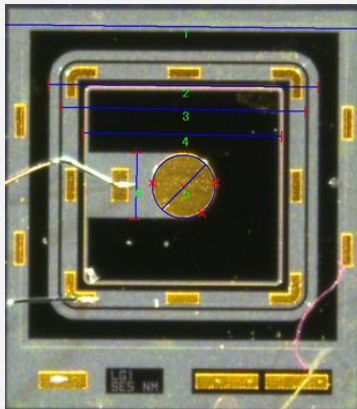


Tested LGAD Samples

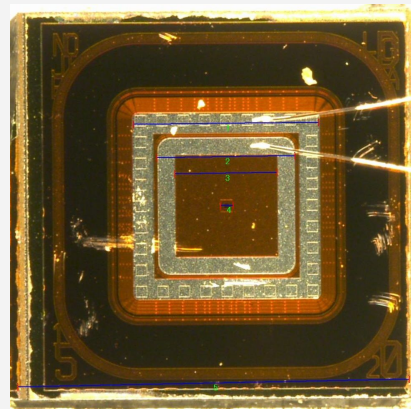
- Tested 1 PiN device, 3 (DC) LGAD types:
 - All samples are single pad devices with active area of $1.3 \times 1.3 \text{ mm}^2$
 - Two implant depths of the gain layer: shallow $\sim 1 \mu\text{m}$, deep $\sim 2 \mu\text{m}$.
- Tested 50 μm BNL strip AC-LGAD. (very preliminary)

Device	Active Thickness [μm]	Gain Layer	Breakdown [V]
HPK LGAD type 3.1	50	shallow	~ 230
HPK LGAD type 3.2	50	deep	~ 130
HPK PiN	50	No gain	~ 400
BNL LGAD	20	shallow	~ 100

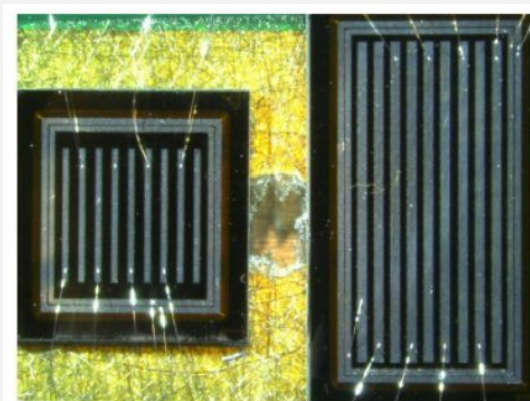
HPK Pad Device



BNL Pad Device



BNL AC-LGAD Strips Device





The SSRL Testbeam Setup

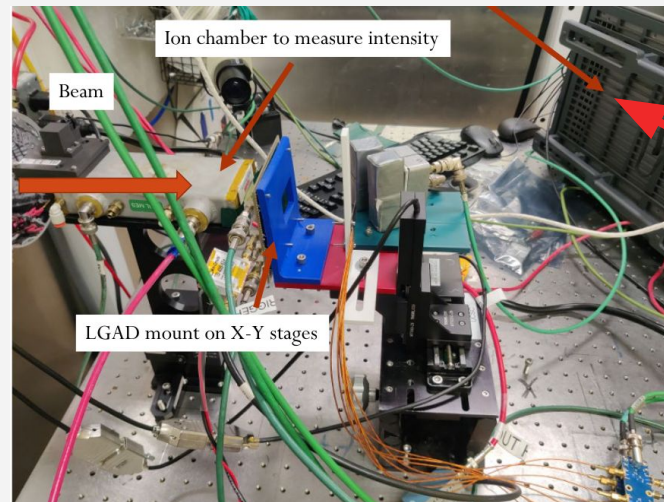
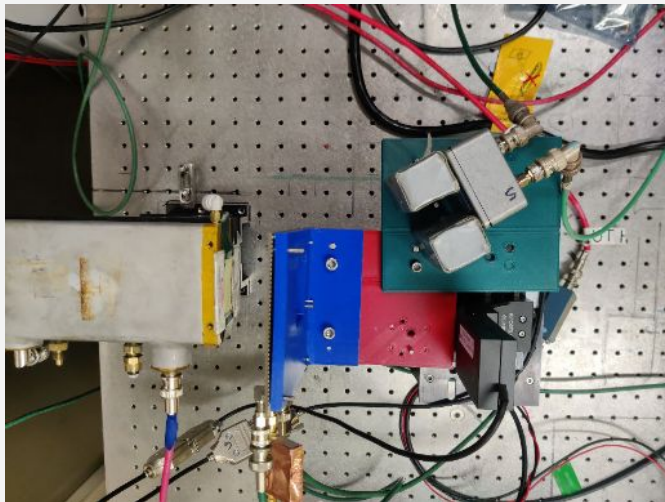


- The Stanford Synchrotron Radiation Lightsource (SSRL) 11-2 beamline:

- X-rays energy:
 - 5 to 70 keV
 - Energy resolution of $\Delta E/E \approx 10^{-4}$
 - Monochromator to filter harmonics
- Beam structure:
 - Spot size 25mm x 1mm
 - 4 groups of 70 bunches
 - 10 ps length (RMS)
 - Separated by 2.1 ns



- All measurements were performed at room temperature.

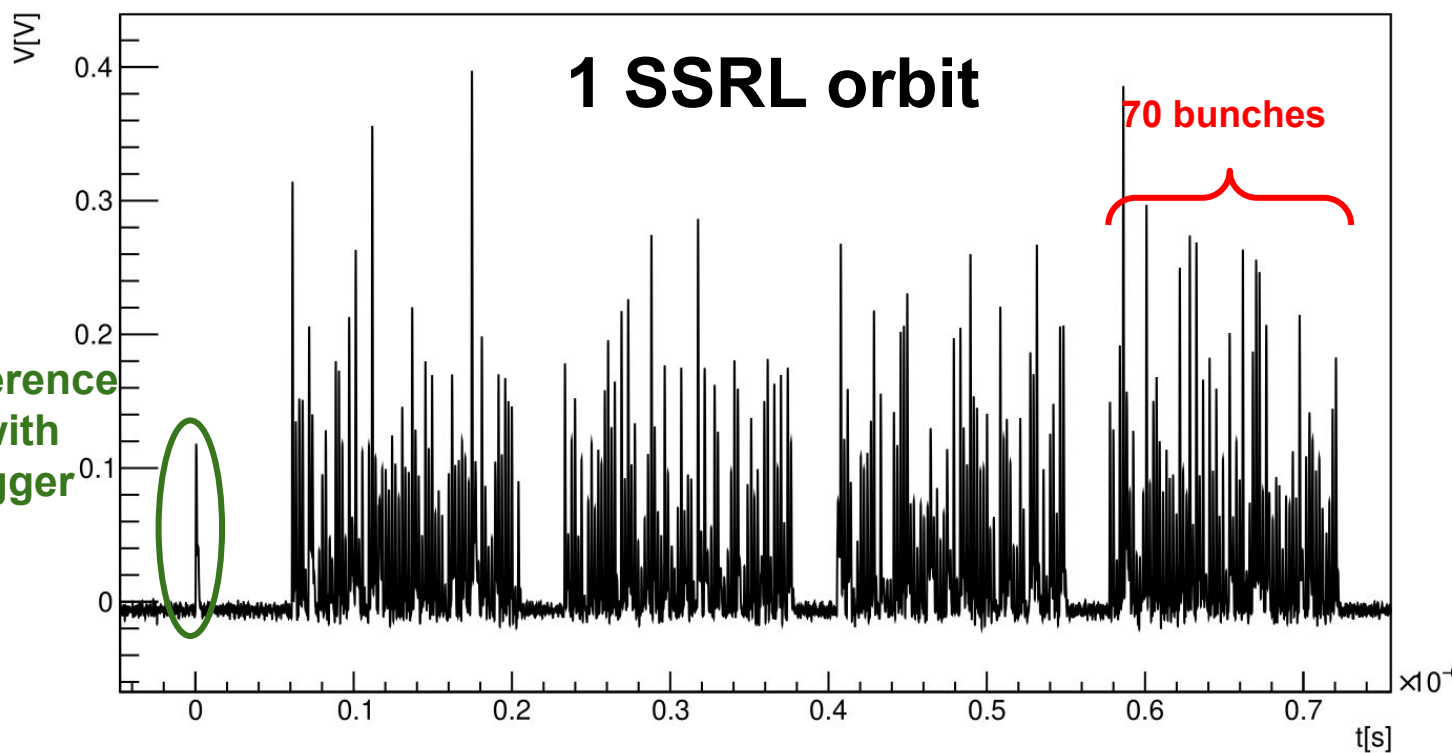
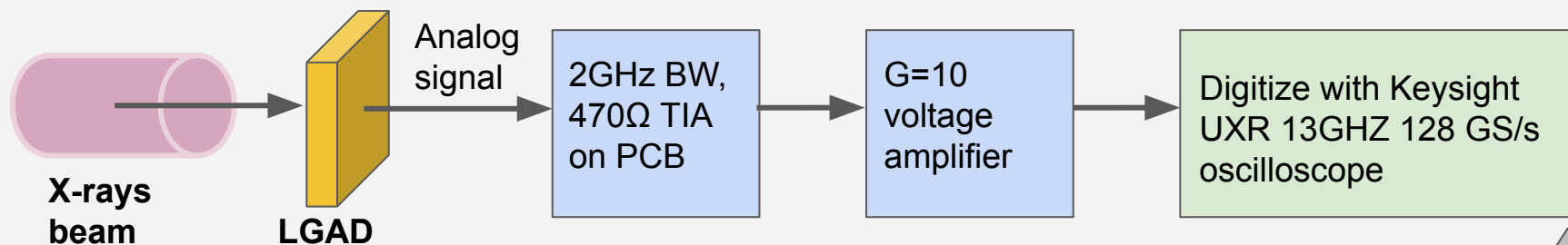


Digitize with
Keysight UXR
13GHZ
128 GS/s
oscilloscope

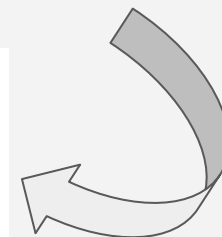


The SSRL Testbeam Setup

- Data acquisition:



Time reference
synced with
beam trigger



Energy Linearity & Resolution

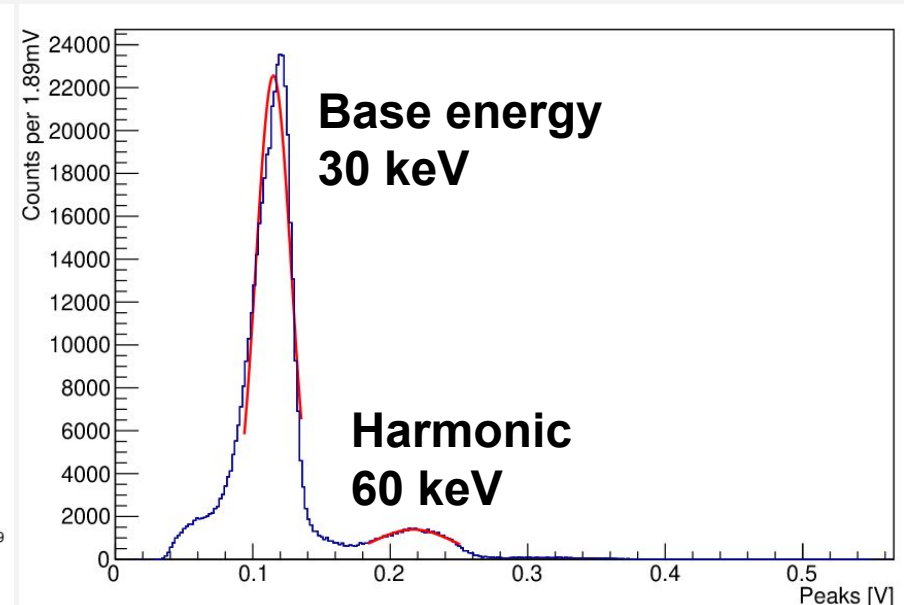
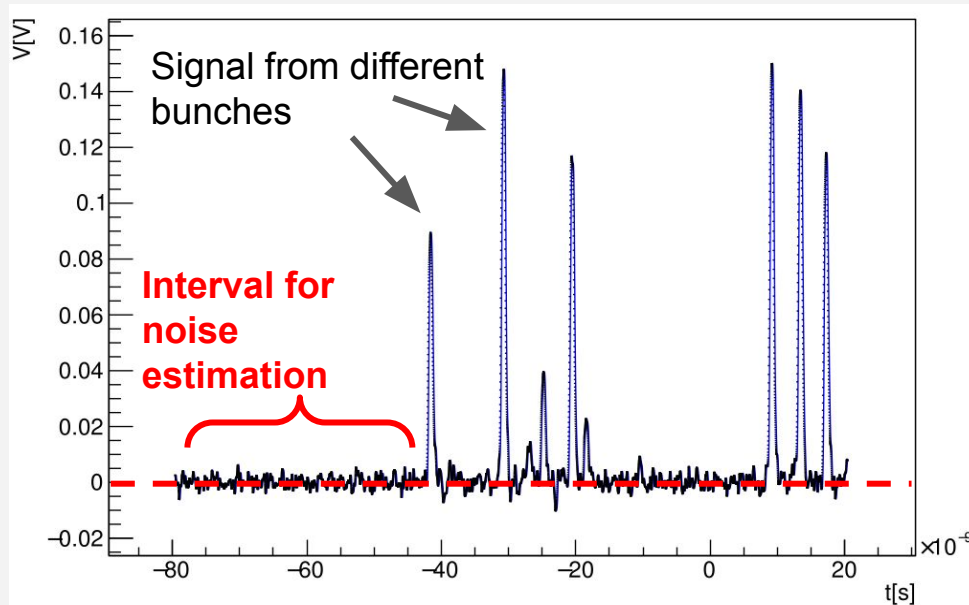




X-rays Energy Estimation

- **The signal maximum (peak) is used as estimator for X-rays energy.**
 - Baseline correction from [\[1\]](#) is applied to reduce fluctuation from amplification circuit.
 - Signal peak at least $> 7\sigma_{\text{noise}}$
 - Time separation between adjacent peaks at least 2.1 ns
- Using mean(μ) and width(σ) of the Gaussian fit to the peaks distribution:
 - **Energy : μ**
 - **Resolution: σ/μ**

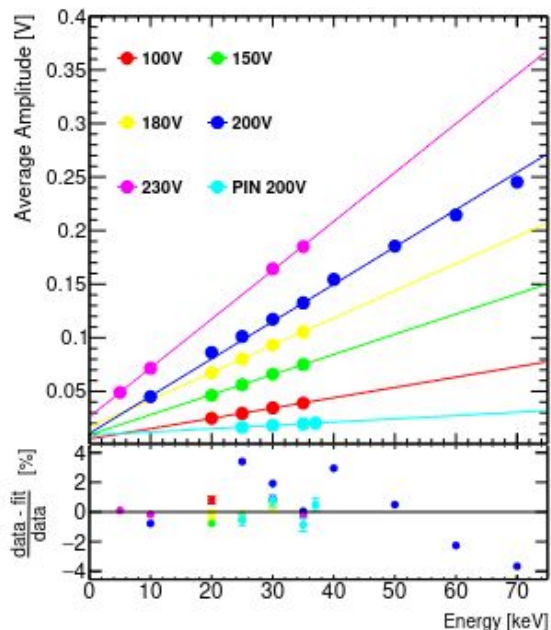
**Example distribution for 30 keV X-rays
HPK 3.1 at 200V**



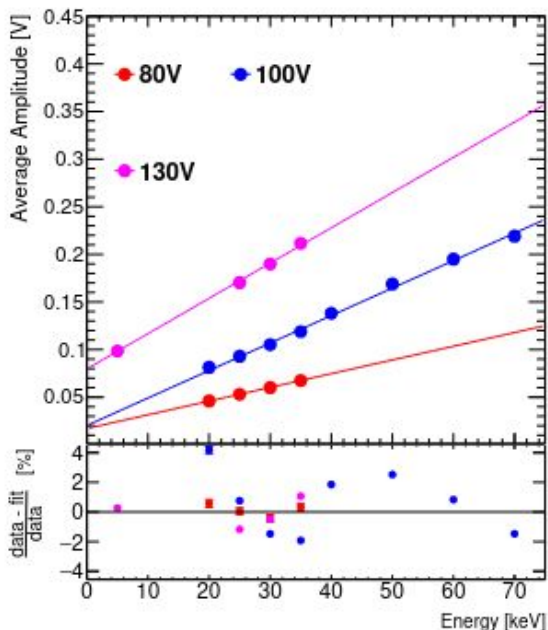


X-rays Energy Linearity

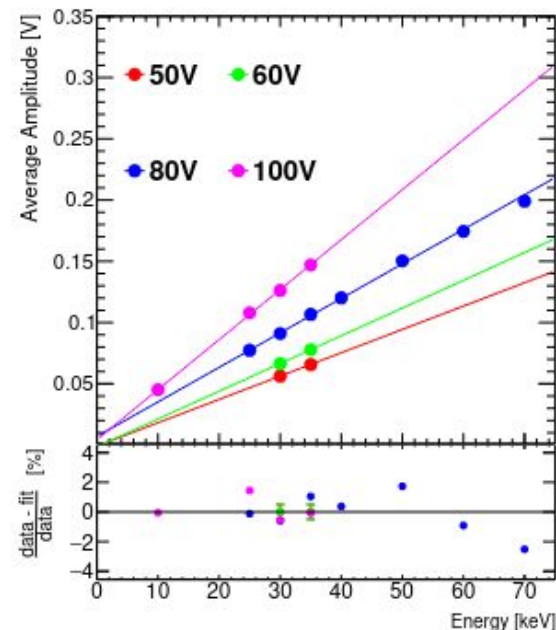
- The μ is extracted for each energy, bias voltage, and sensor type.
- The relation of μ to X-rays energy is shown below:



(a) HPK PIN and type 3.1 LGAD



(b) HPK type 3.2 LGAD

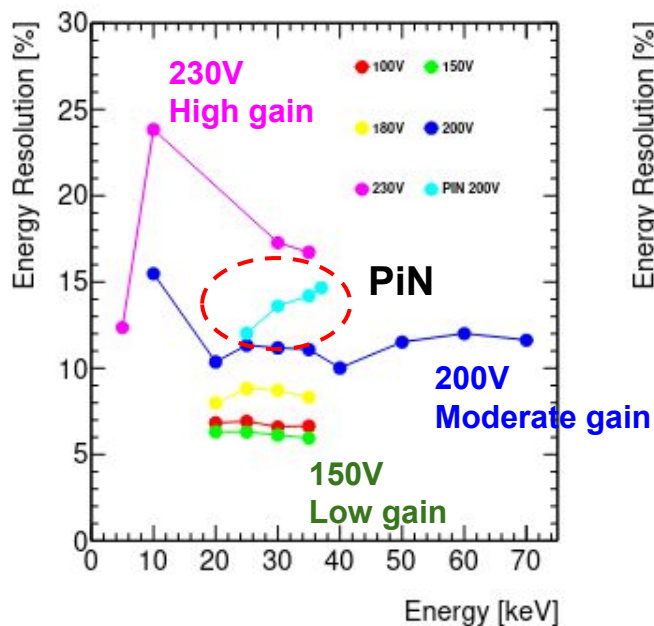


(c) BNL 20um LGAD

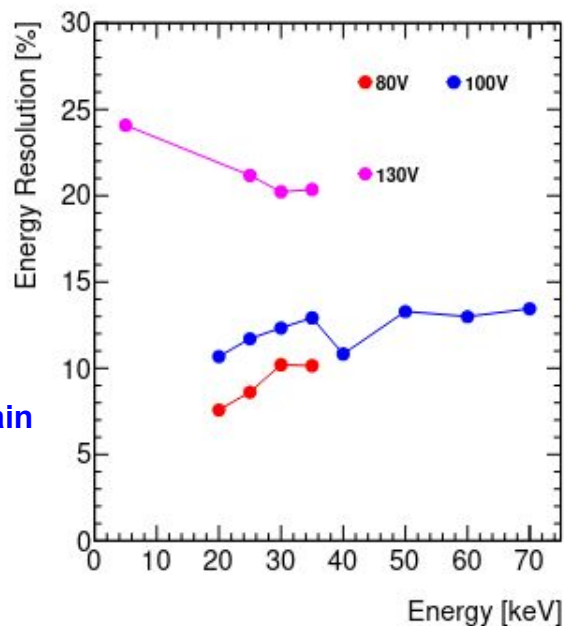


X-rays Energy Resolution

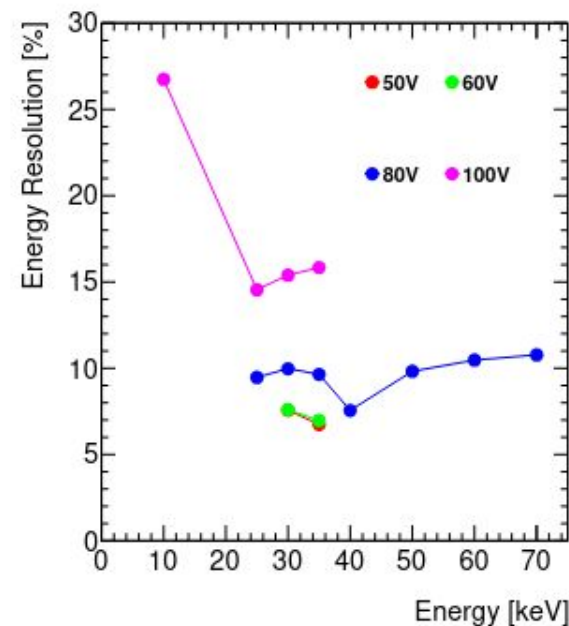
- The energy resolution (σ/μ) of LGADs for each of the tested X-rays energies are shown:
 - The energy resolution is approximately constant over the tested energy range.
 - The energy resolution degrades at higher gains.



(a) HPK PIN and type 3.1 LGAD



(b) HPK type 3.2 LGAD



(c) BNL 20um LGAD

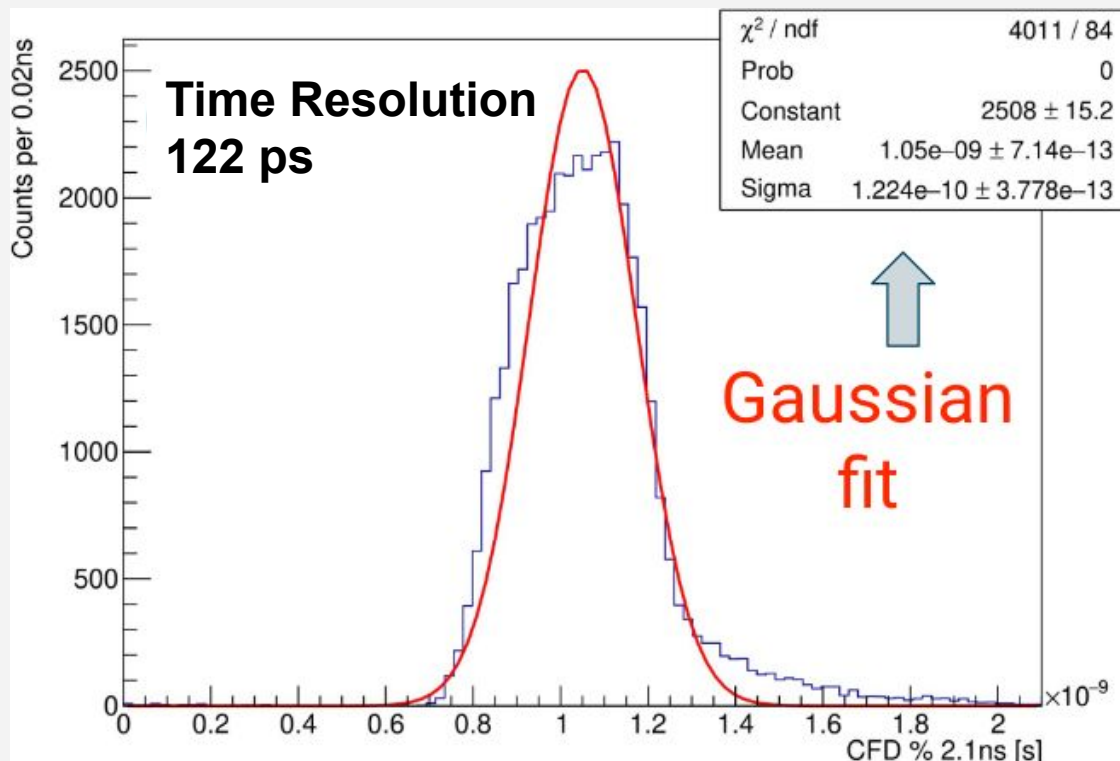
Timing Performance





Extracting the Timing Resolution

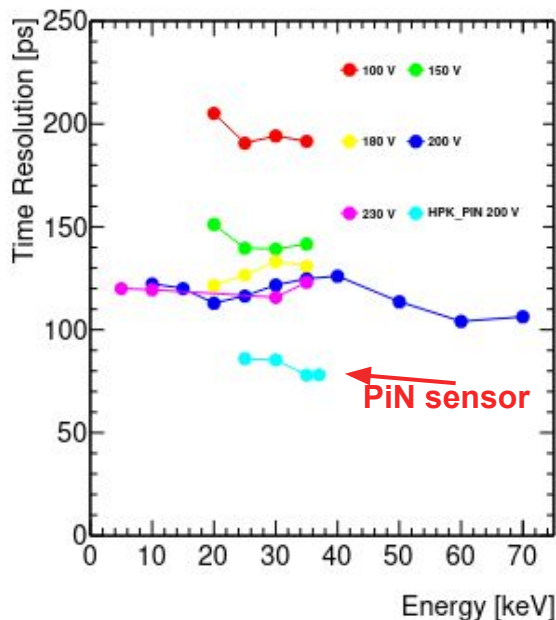
- **Constant fraction discriminator (CFD) at 20% is used for timing.**
 - The fast rising edge of the initial carrier drift is more stable and precise.
- **Time difference with respect to the reference time is calculated for each bunch**
 - The bunch separation of 2.1 ns is accounted.
 - Distribution is fitted with a Gaussian, the sigma is the timing resolution.



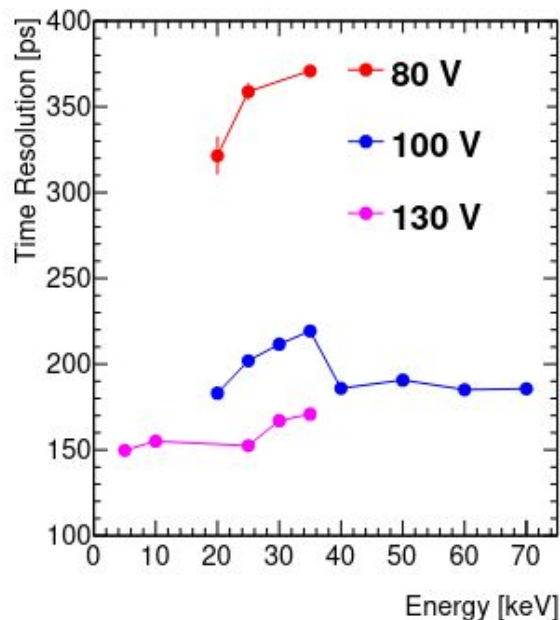


Timing Resolution for X-rays

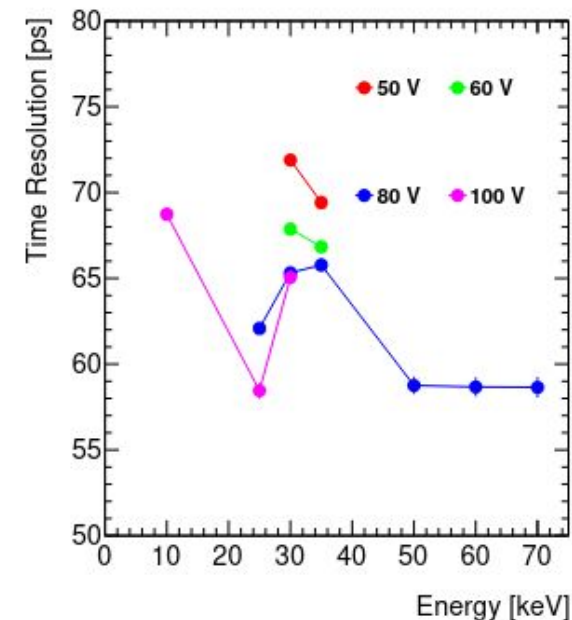
- The timing resolution is consistent for the tested X-rays energy range.
- Thinner sensors (20 vs 50 μm) have better timing performance as expected.
- However:
 - The timing performance for X-rays is worse comparing to MiPs (< 50 ps)
 - In the case of 50 μm sensors, PiN provides better timing.
- **Why are we seeing bad timing resolution?**



(a) HPK PIN and type 3.1 LGAD



(b) HPK type 3.2 LGAD



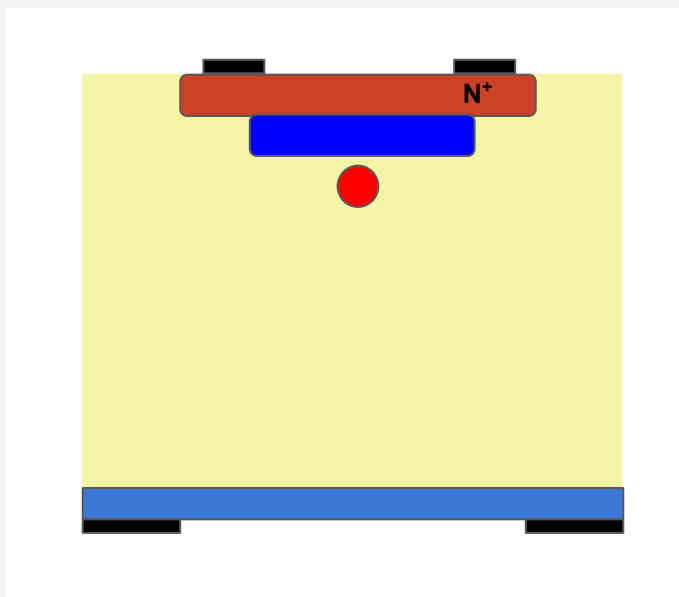
(c) BNL 20 μm LGAD



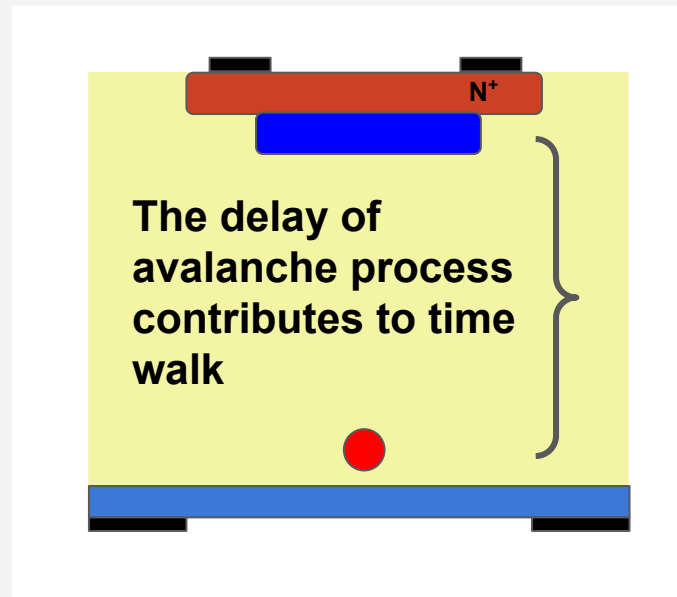
Time Walk Due to X-rays Conversion

- The absorption of X-rays photons at different depth inside the sensor introduces time delay in the avalanche process.
- The time delay in the avalanche process will affect the signal formation shape and contributes to the timing performance.

X-rays absorption
near **surface**



X-rays absorption
near **backside**

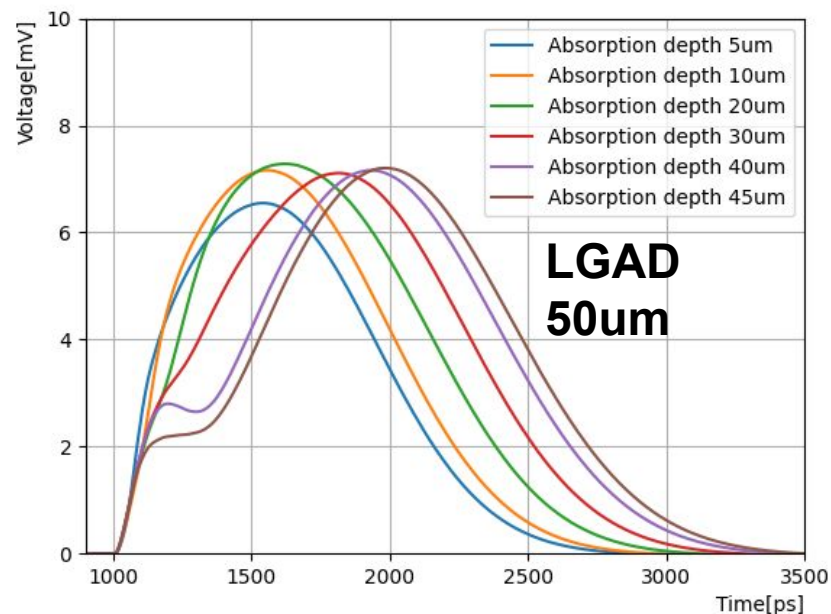
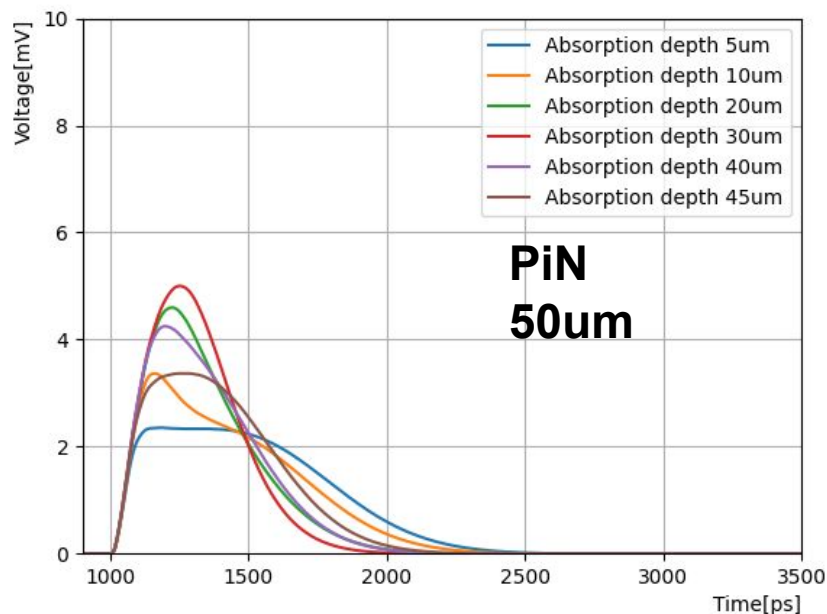




Time Walk Due to X-rays Conversion

- **In the case of PiN (no gain), the rising edge not affected by the delay.**
 - The variation in the peak and width is due to the collection of electrons vs holes.
- **The rising edge and the peak of LGADs is sensitive to the X-rays absorption depth:**
 - Using CFD 20% reduces the time walk effect but doesn't remove it completely.
 - **Absorption on the back has more gain (charge cloud expansion & gain suppression)**

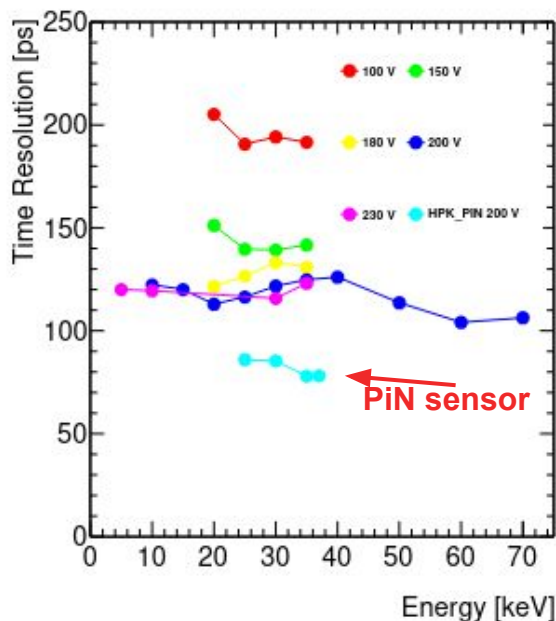
**TCAD simulated signal of PiN and LGAD at different absorption depth.
(X-rays energy = 20 keV)**



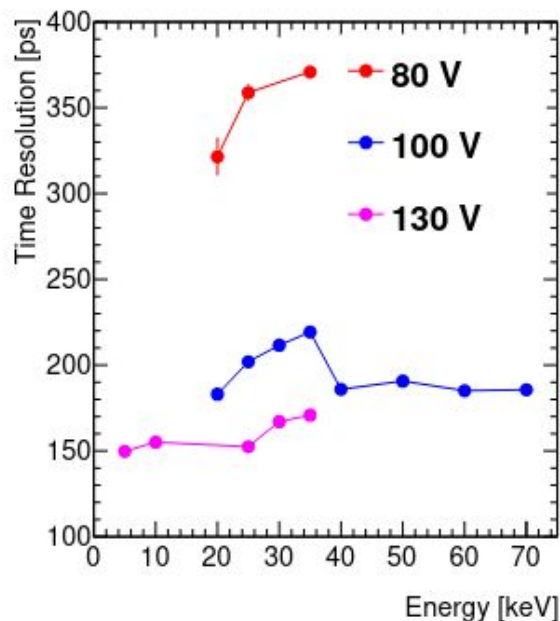


Timing Resolution for X-rays

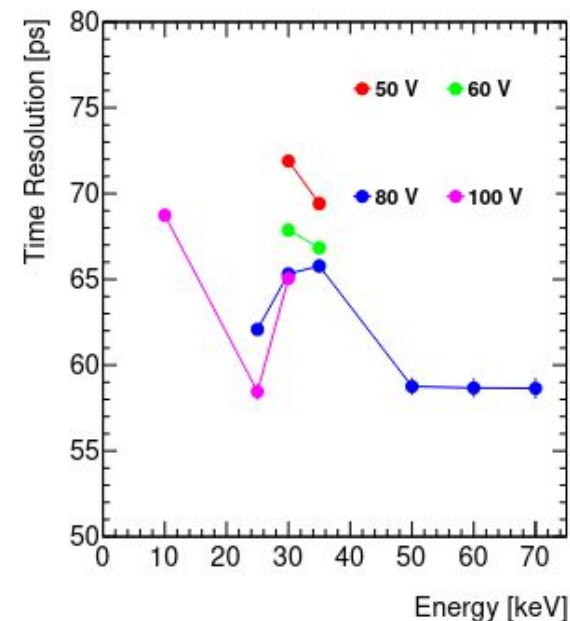
- **LGAD bulk E-field is usually high enough to saturate the carrier drift velocity (1×10^7 cm/s).**
- **Assuming X-rays photon absorption depth is approximately equally probable (which is not true and it depends on the X-rays energy), the time resolution due to avalanche process delay is approximately: 50um is ~ 125 ps, 20um is ~ 50 ps**
- **Although PiN devices have better timing resolution, LGADs have advantage on signal amplification. Also, thinner LGADs will improve the timing resolution for X-rays.**



(a) HPK PIN and type 3.1 LGAD



(b) HPK type 3.2 LGAD



(c) BNL 20um LGAD

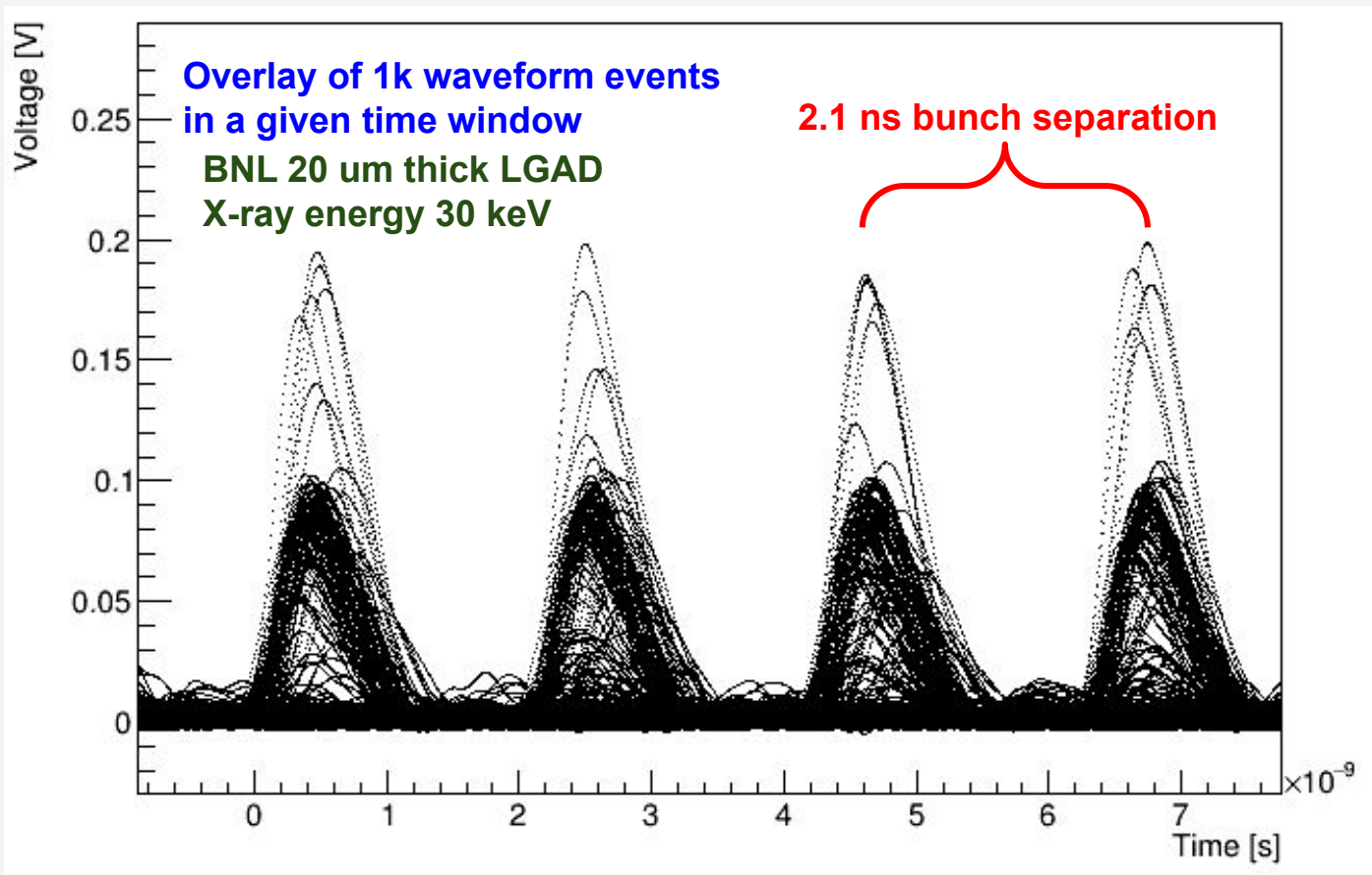
Timing Performance: High Frame Rate Capability





High Repetition Rate Capability

- The LGAD charge collection time is fast due to very thin active thickness and saturated carrier drift velocity.
- LGADs is able to resolve 500 MHz repetition rate (with capability up to 1GHz).



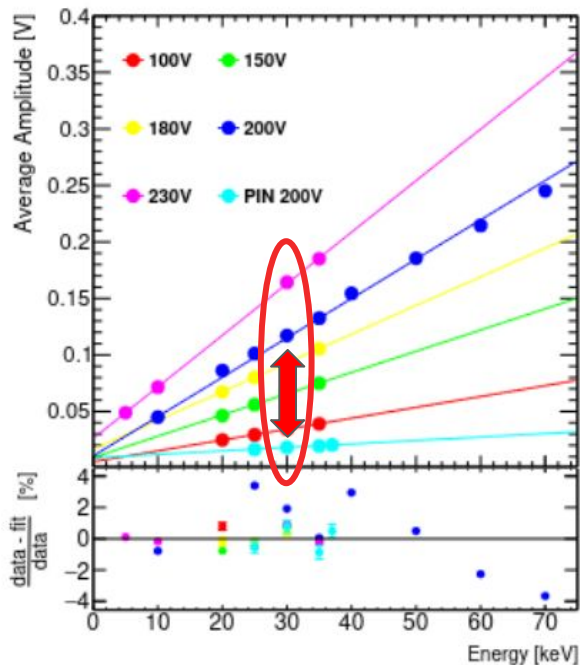
Gain Suppression



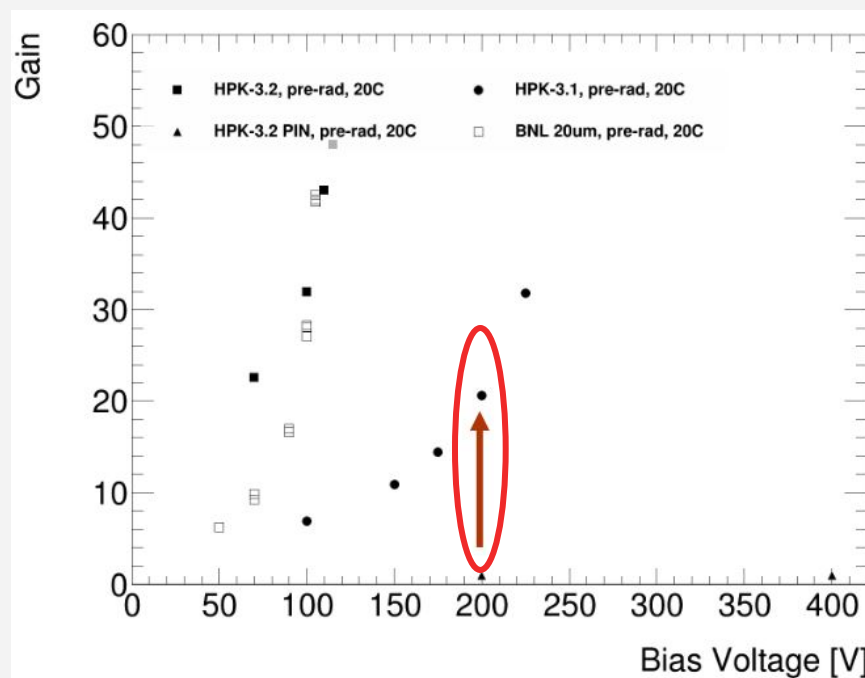


Why is the Gain Different?

- The gain of LGAD is measured in reference to the PIN device in the laboratory.
- The gain of LGAD for conventional MIP like charge particles is different from X-rays. In the case of HPK 3.1 at 200V:
 - The gain for MIPs is ~20.
 - The gain for 30 keV X-rays is ~10



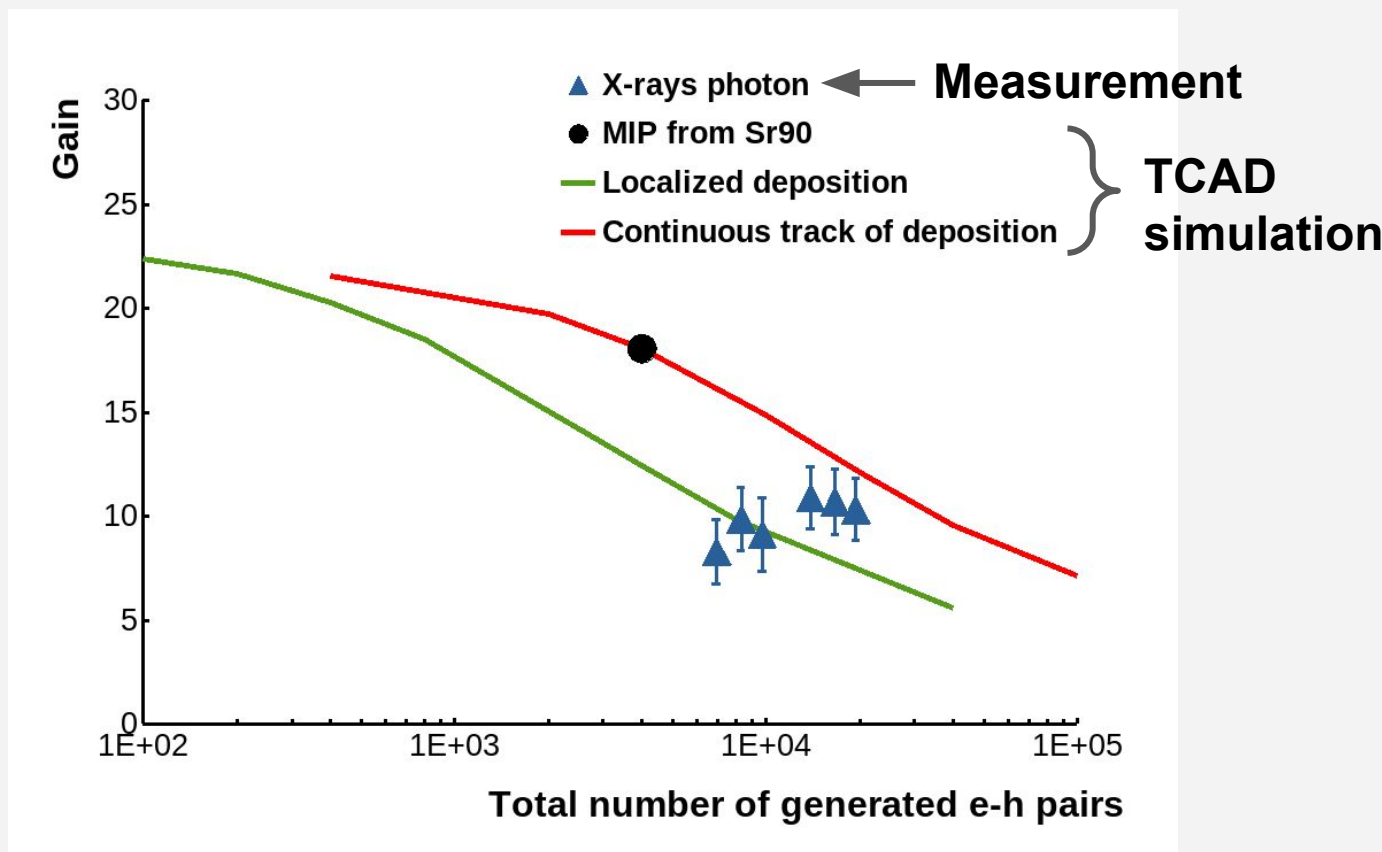
(a) HPK PIN and type 3.1 LGAD





Gain Suppression

- TCAD simulation is used to study the MiP-like vs X-rays-like deposition.
 - Localized deposition is used to approximate X-rays deposition.
 - Continuous track is used to approximate MIP deposition.

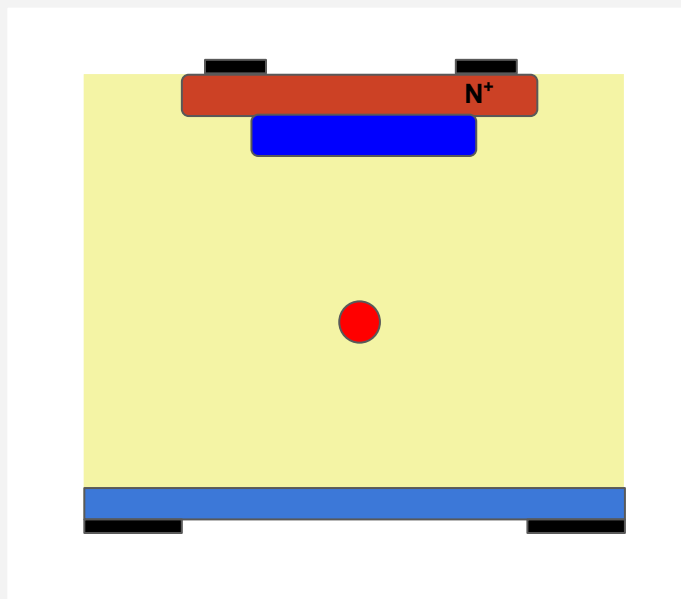




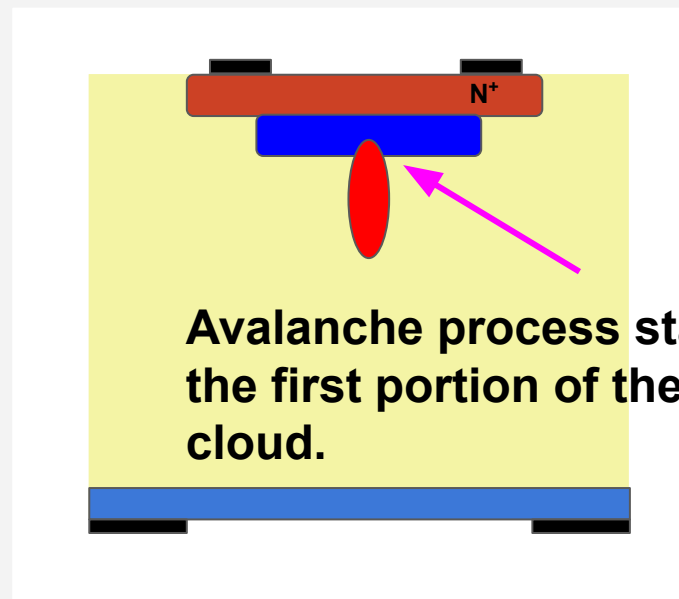
Gain Suppression

- One possible explanation to gain suppression is related to the generated e-h density and the gain layer E-field relaxation process.

Initial Deposition from X-rays



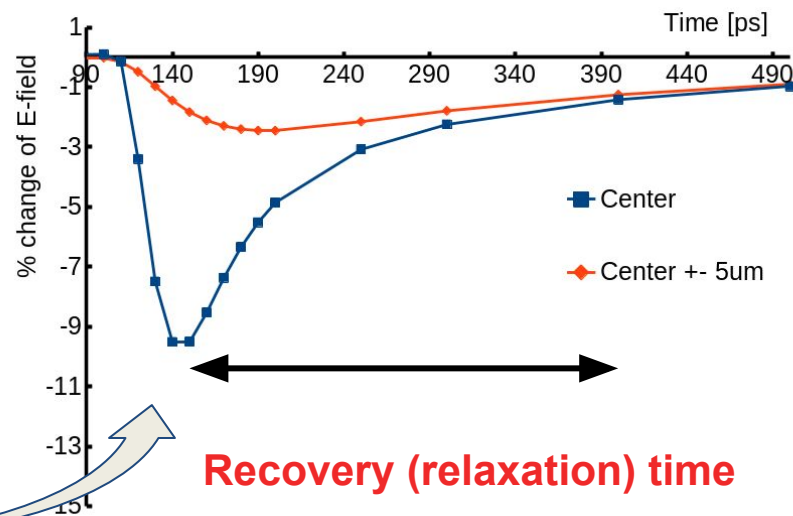
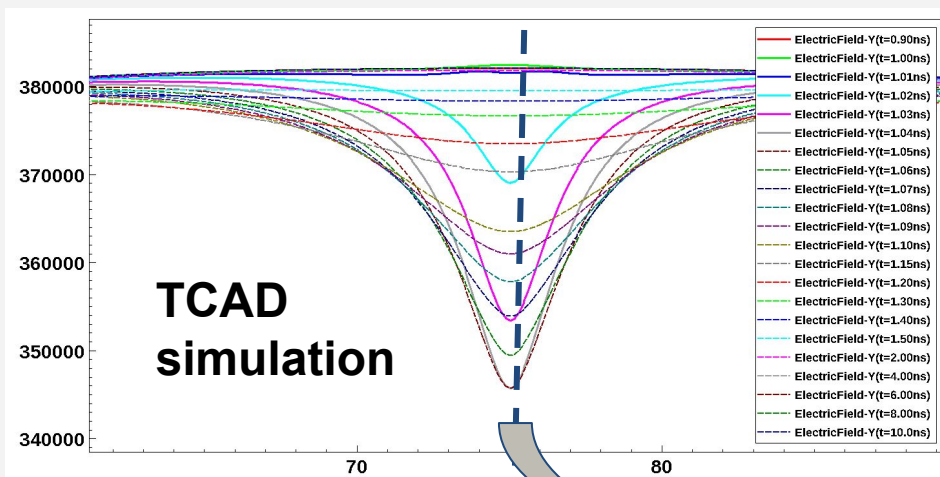
Charge cloud drift toward gain layer.
Shape expand due to diffusion





Gain Suppression

- One possible explanation to gain suppression is related to the generated e-h density and the gain layer E-field relaxation process.
- This variation of E-field depends on the generated e-h paris density per unit distance.
- MiP generates less e-h paris per unit distance comparing to point-like X-rays deposition.



Snapshot of the electric field within the gain layer at different time for localized input charge.

Note: the impact ionization has exponential dependence on the field.



Gain Suppression



- One possible explanation to this is related to the generated e^-h density and

Gain suppression studied by other groups: e.g. “Hunting for Sharks with TCAD (Simulation of TPA-TCT measurements on LGAD Gain Suppression)”

<https://indico.cern.ch/event/1334364/contributions/5672074/>

Gain suppression with larger dynamic range (e.g. non MIP particles with bragg-peak in energy deposition):

See Jennifer Ott’s talk on the PIONEER experiment:

<https://indico.cern.ch/event/1184921/contributions/5574780/>

Snare
with
time for localized input charge.

field.

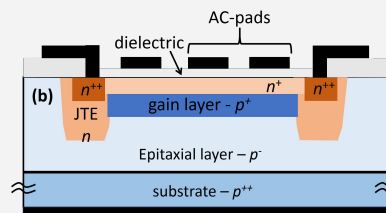
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How about AC-LGAD?

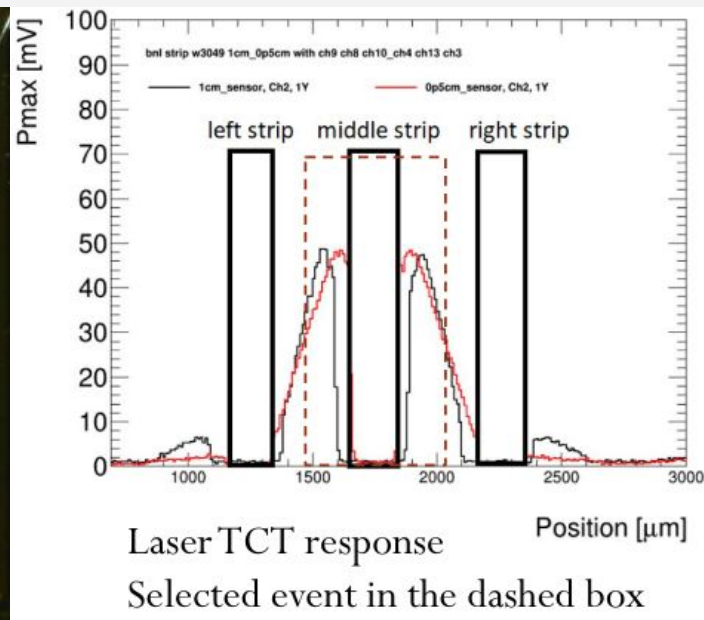
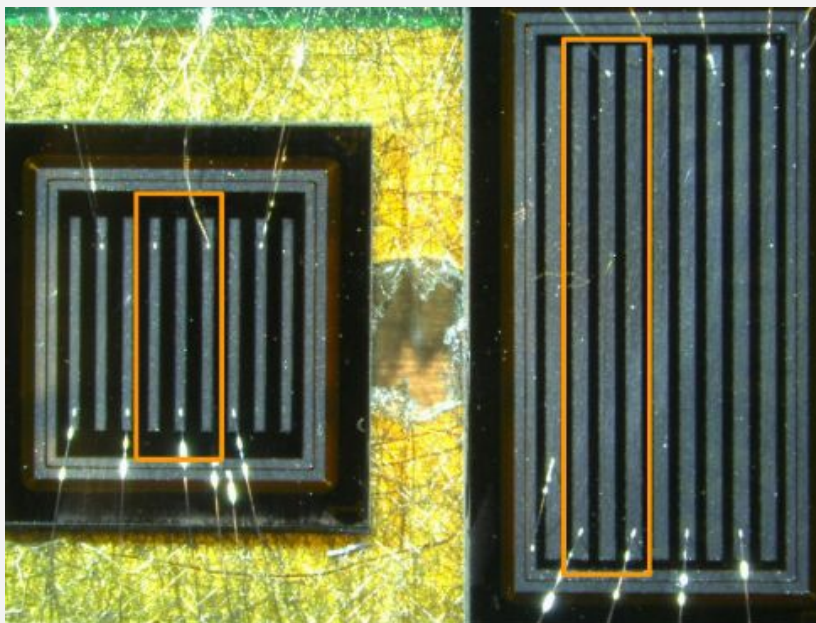




How about AC-LGAD?



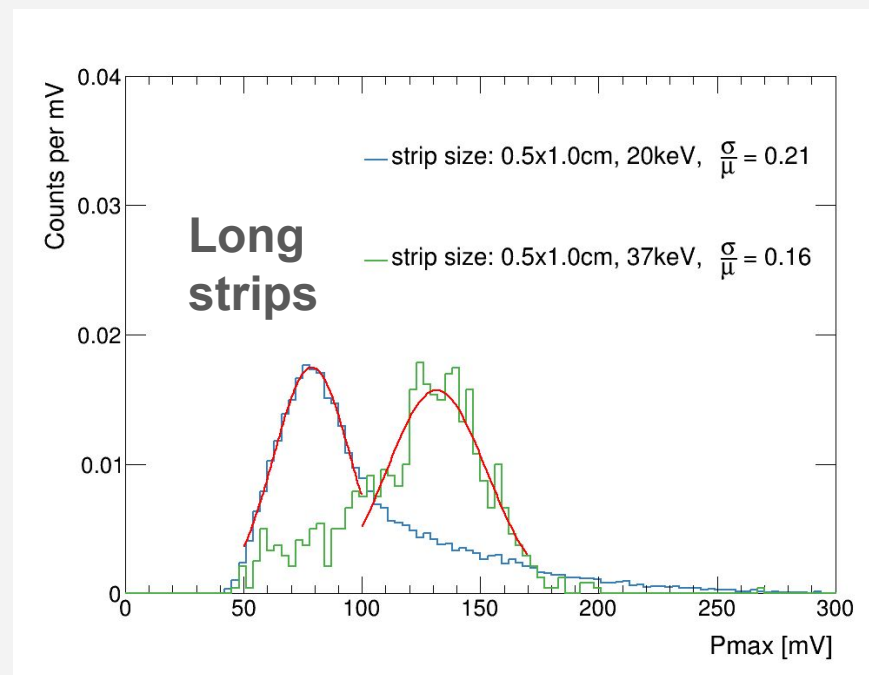
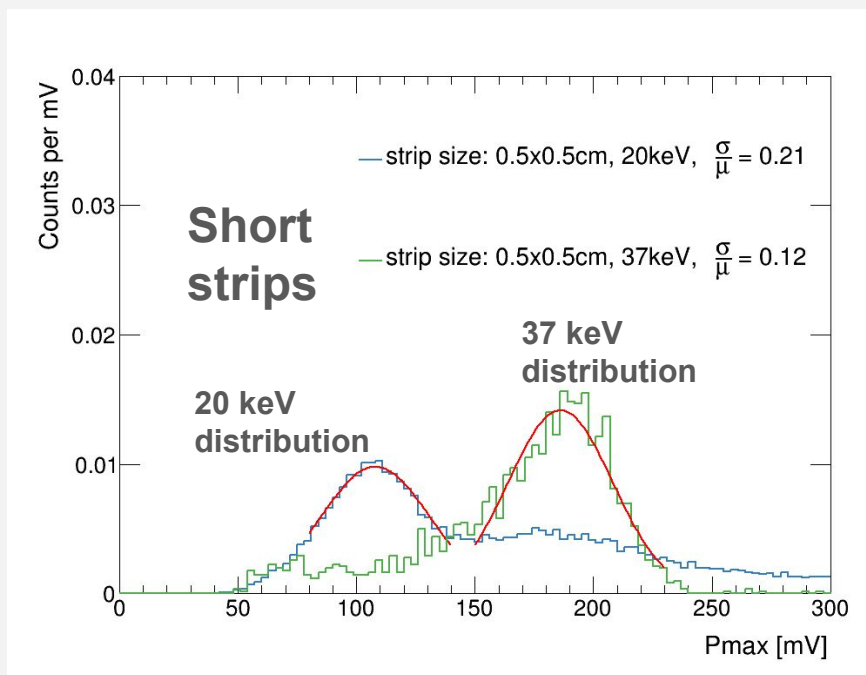
- **Very preliminary test of AC-LGAD strip sensors using the same beam line:**
 - Readout all strips with 16 channels FNAL board and CAEN DT5742 digitizer.
 - Unfortunately, beam spot is broad so no information on position.
- **Base on the TCT studies on the same devices, the charge sharing mostly contained in 3 strips:**
 - Search for events with highest response in the middle strip and lower response in the two neighbors, and response from the remaining strips.
 - Sum the three strips signals to estimated the total energy.





How about AC-LGAD?

- The energy response is roughly linear as expected.
- The energy resolution is between 12% to 21%. It's slightly worse than DC devices probably due to charge sharing.
- The shorter strip device has slight better energy resolution at high energy due to smaller sharing.



Summary





Summary



- The SSRL testbeam results for LGADs were shown:
 - Energy resolution is between 6% to 20%, and out performing conventional PiN devices (and better SNR).
 - Time resolution is between 50 to 200 ps. (depends on thickness)
 - Easily resolve 500 MHz repetition rate of the X-rays beam line.
- The gain of LGADs depends on the type of energy deposition. The gain is lower for X-rays in comparison to MiP.

35 keV X-rays

	HPK PIN	HPK3.1		HPK3.2		BNL 20um	
Bias V	200 V	150 V	230 V	80 V	130 V	50 V	100 V
Energy Resolution	14 %	6 %	17 %	10 %	20 %	6 %	16 %
Energy Response	19 mV	75 mV	185 mV	68 mV	211 mV	66 mV	147 mV
σ_t CFD	78 ps	141 ps	123 ps	371 ps	171 ps	69 ps	65 ps



Future Developments



- **Next test beam scheduled for February 2024:**
 - **Beam line 7-2 with focused beam of spot size 50x100um**
 - **Allows for better study of standard LGADs with X-rays always contains in the active region with gain.**
 - **Test of LGAD and AC-LGAD array with position information.**
- **Looking for Compton response using SiPM trigger/tag.**
- **Extend the energy range down to sub-KeV.**

Backup





Reference



- [1] S.-J. Baek, A. Park, Y.-J. Ahn and J. Choo, Baseline correction using asymmetrically reweighted penalized least squares smoothing, *Analyst* 140 (2015) 250–257.



Funding and Acknowledgement





Funding & Acknowledgement

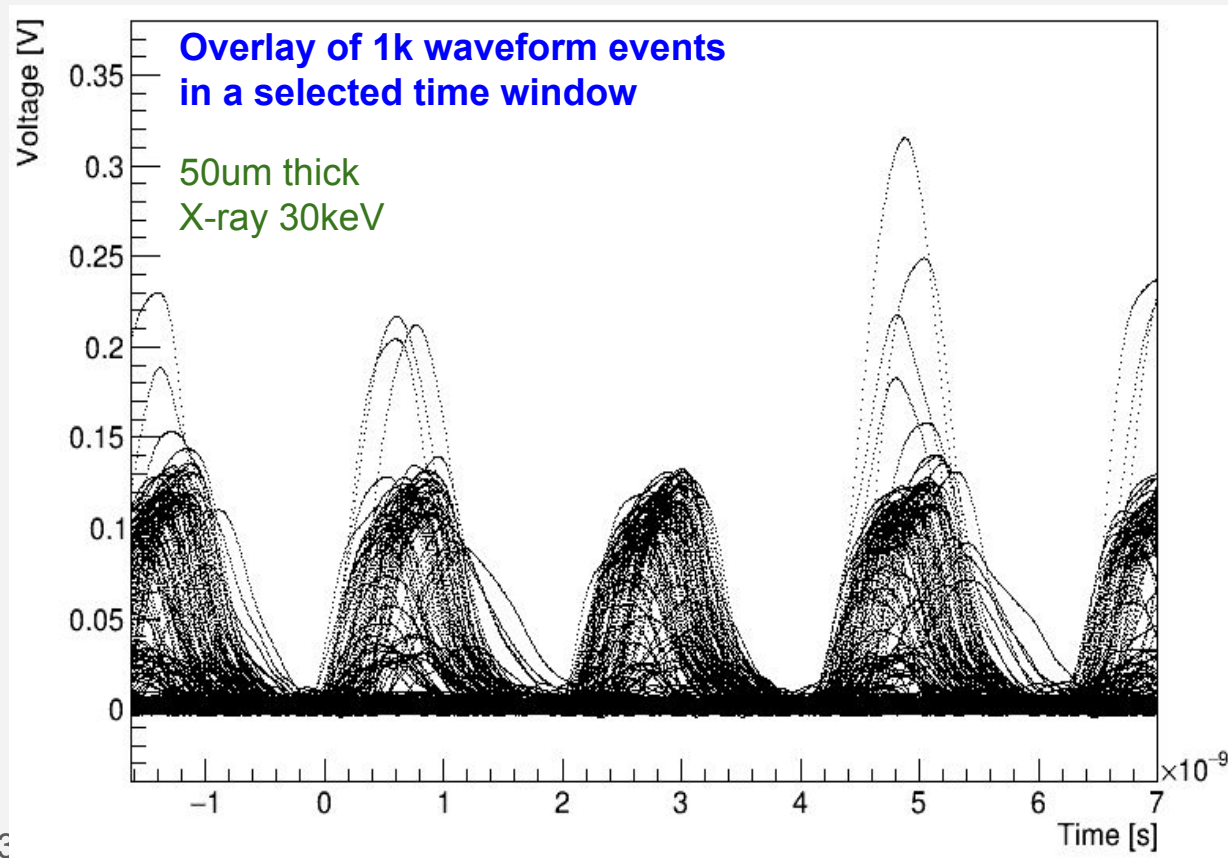


- The United States Small Business Innovation Research (SBIR) Program.
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- Launchpad Grant awarded by the Industry Alliances & Technology Commercialization office from the University of California, Santa Cruz.
- The of the Stanford Synchrotron Radiation Lightsource, SLAC National Accelerator Laboratory, is supported by the U.S. Department of Energy, Office of Science, Office of Basic Energy Sciences under Contract No. DE-AC02-76SF00515.
- The group from USP acknowledges support from FAPESP (grant 2020/04867-2) and CAPES.



High Repetition Rate

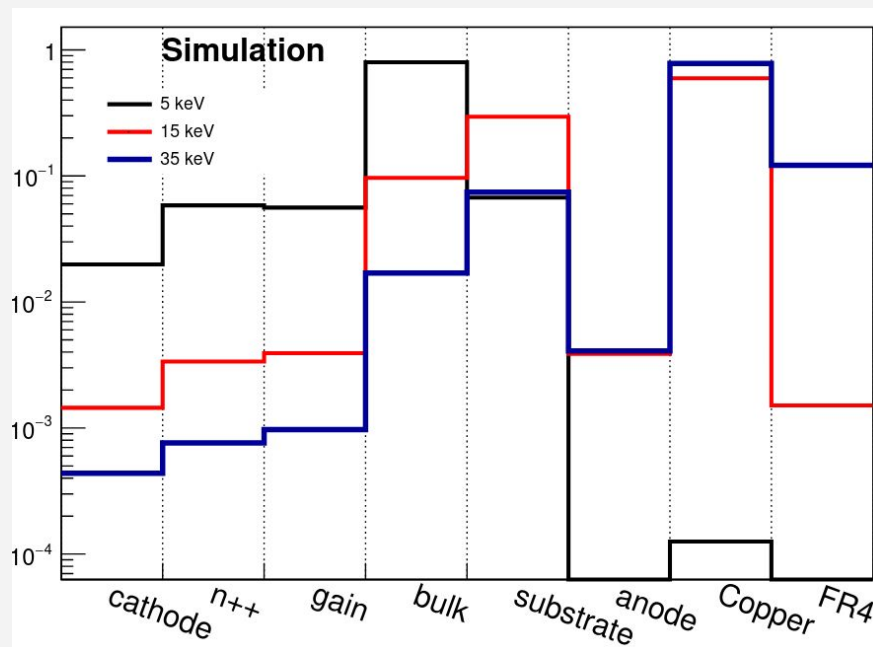
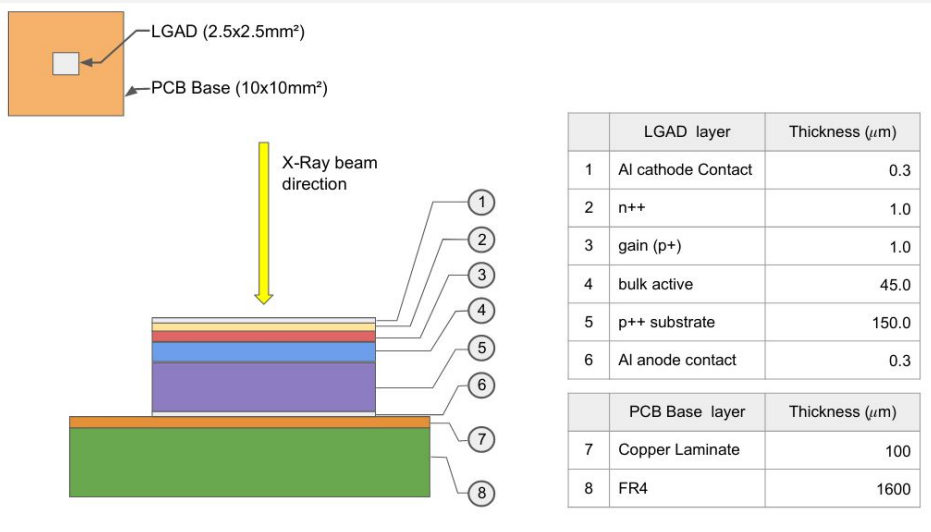
- Frame rate capability is lower for thicker LGAD (50um)
- It's still capable to fully resolve 500MHz frame rate.





GEANT4 Simulation of X-rays Absorption Location

- GEANT4 simulation of the X-rays absorption location.





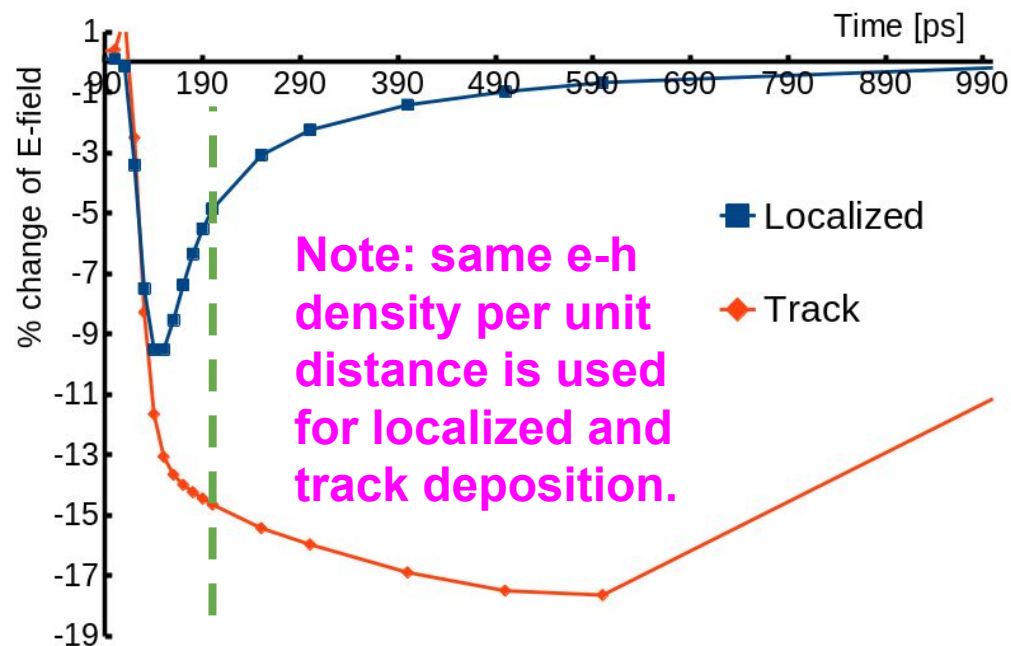
Gain Suppression

- One possible explanation to this is related to the generated e-h density and the gain layer E-field relaxation process.
- This variation of E-field depends on the generated e-h paris density per unit distance.
- MiP generates less e-h paris per unit distance comparing to point-like X-rays deposition.

1) charge arrived at the gain layer at later time see a relatively lower field due to the previous impact ionization process.

→ gain suppression

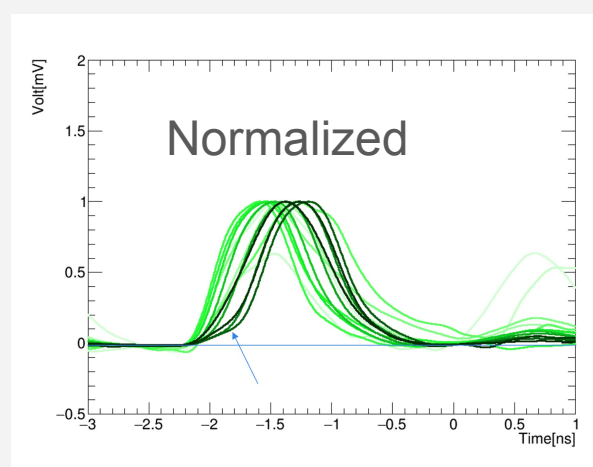
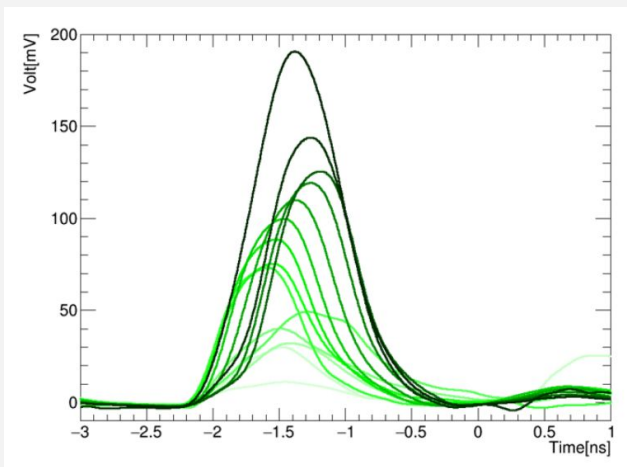
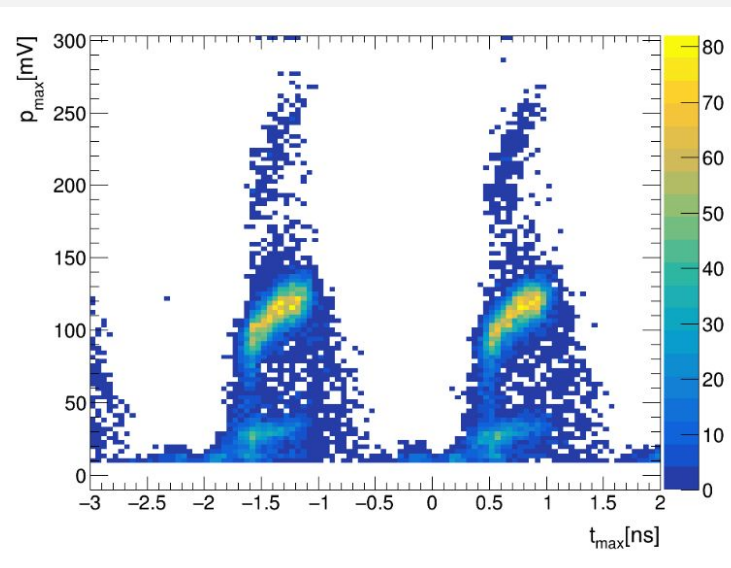
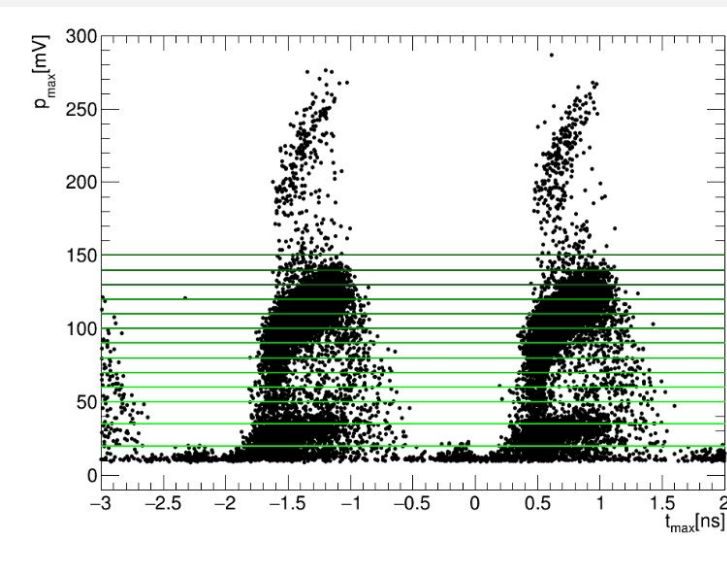
2) Faster recovery time should reduce the gain suppression effects.





Tmax vs Pmax & Averaged Waveform

- Correlation plots of the Tmax vs Pmax





Gain Suppression & Absorption Depth



- Absorption on the back has more gain for LGADs due to charge cloud expansion

